



CPH3348 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Ultrahigh-speed switching.
- 1.8V drive

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-12	V
Gate-to-Source Voltage	V_{GSS}		± 10	V
Drain Current (DC)	I_D		-3	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	-12	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (1200mm ² ×0.8mm)	1.0	W
Channel Temperature	Tch		150	$^\circ\text{C}$
Storage Temperature	Tstg		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1\text{mA}$, $V_{GS}=0\text{V}$	-12			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-12\text{V}$, $V_{GS}=0\text{V}$			-10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8\text{V}$, $V_{DS}=0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-6\text{V}$, $I_D=-1\text{mA}$	-0.4		-1.4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-6\text{V}$, $I_D=-1.5\text{A}$	2.7	4.5		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-1.5\text{A}$, $V_{GS}=-4.5\text{V}$		54	70	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D=-0.8\text{A}$, $V_{GS}=-2.5\text{V}$		80	115	$\text{m}\Omega$
	$R_{DS(on)3}$	$I_D=-0.3\text{A}$, $V_{GS}=-1.8\text{V}$		125	215	$\text{m}\Omega$

Marking : WE

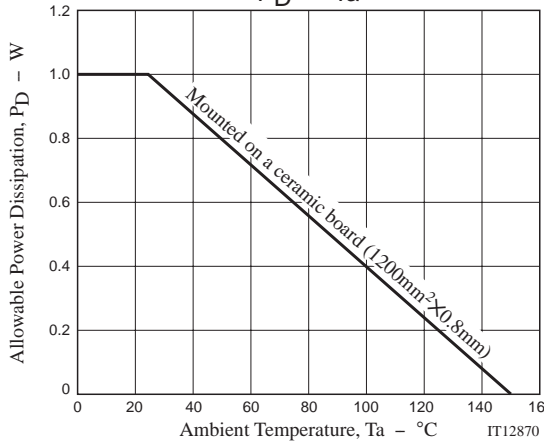
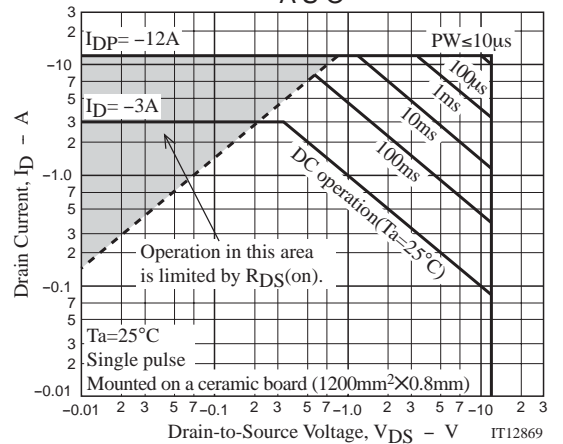
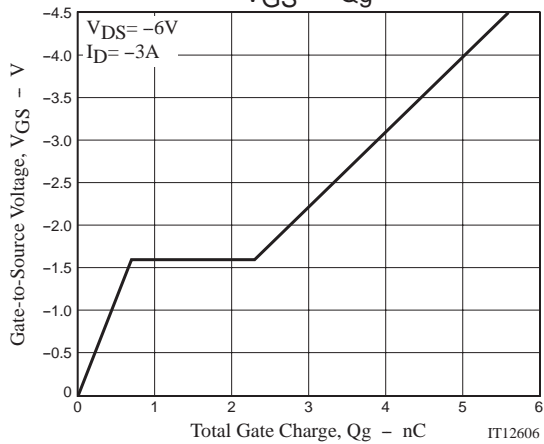
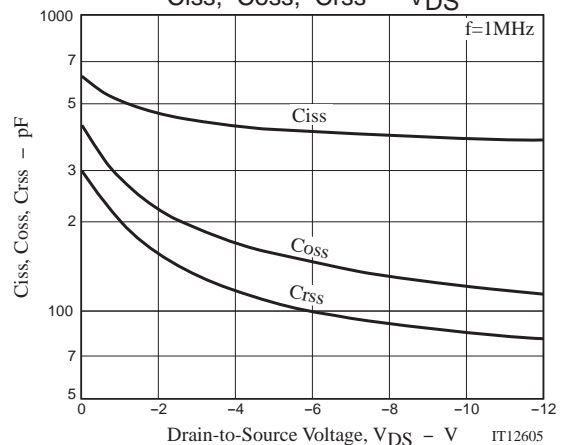
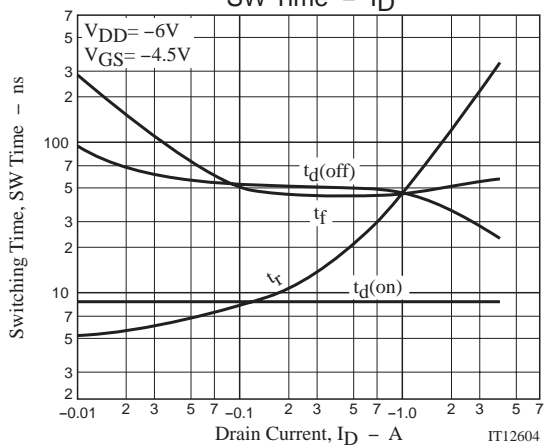
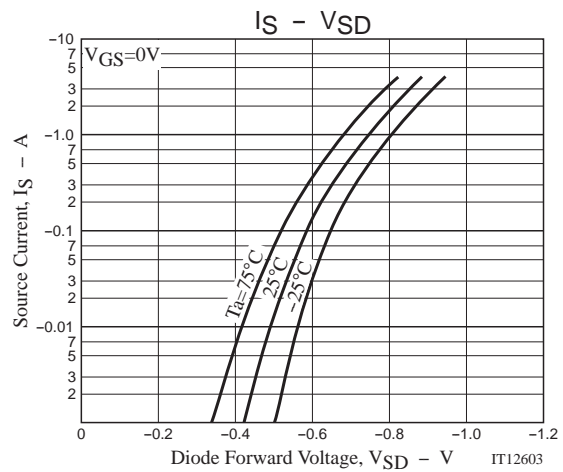
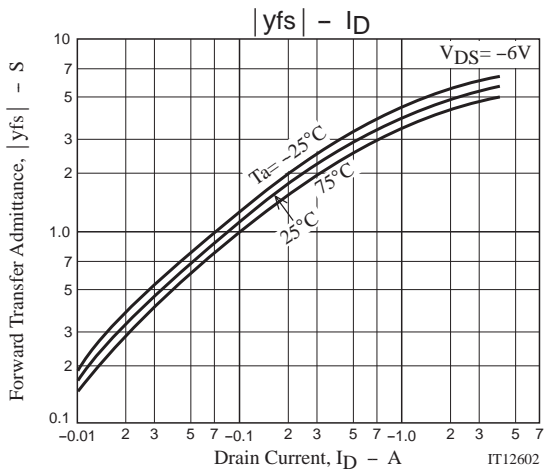
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Note on usage : Since the CPH3348 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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